

# Dingkun Ren

## List of Publications by Year in descending order

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Version: 2024-02-01

21  
papers

250  
citations

1163117

8  
h-index

940533

16  
g-index

21  
all docs

21  
docs citations

21  
times ranked

415  
citing authors

#	ARTICLE	IF	CITATIONS
1	Room-Temperature Midwavelength Infrared InAsSb Nanowire Photodetector Arrays with Al <sub>2</sub> O <sub>3</sub> Passivation. Nano Letters, 2019, 19, 2793-2802.	9.1	52
2	InGaAs/GaAs Nanowire Avalanche Photodiodes Toward Single-Photon Detection in Free-Running Mode. Nano Letters, 2019, 19, 582-590.	9.1	40
3	Uncooled Photodetector at Short-Wavelength Infrared Using InAs Nanowire Photoabsorbers on InP with InP Heterojunctions. Nano Letters, 2018, 18, 7901-7908.	9.1	35
4	Seeding layer assisted selective-area growth of As-rich InAsP nanowires on InP substrates. Nanoscale, 2017, 9, 8220-8228.	5.6	16
5	Catalyst-free selective-area epitaxy of GaAs nanowires by metal-organic chemical vapor deposition using triethylgallium. Nanotechnology, 2018, 29, 085601.	2.6	16
6	Feasibility of Tracking Multiple Single-Cell Properties with Impedance Spectroscopy. ACS Sensors, 2018, 3, 1005-1015.	7.8	16
7	Axial InAs(Sb) inserts in selective-area InAsP nanowires on InP for optoelectronics beyond 25 Åµm. Optical Materials Express, 2018, 8, 1075.	3.0	12
8	Feasibility of achieving high detectivity at short- and mid-wavelength infrared using nanowire-plasmonic photodetectors with InAs heterojunctions. Nanotechnology, 2019, 30, 044002.	2.6	9
9	Self-assembly of tensile-strained Ge quantum dots on InAlAs(111)A. Journal of Crystal Growth, 2020, 533, 125468.	1.5	8
10	Selective-area InAsSb Nanowires on InP for 3 – 5 µm Mid-wavelength Infrared Optoelectronics. MRS Advances, 2017, 2, 3565-3570.	0.9	7
11	Exploring time-resolved photoluminescence for nanowires using a three-dimensional computational transient model. Nanoscale, 2018, 10, 7792-7802.	5.6	7
12	High-efficiency ultrafast optical-to-electrical converters based on InAs nanowire-plasmonic arrays. Optics Letters, 2019, 44, 4666.	3.3	6
13	Optical Characterization of AlAsSb Digital Alloy and Random Alloy on GaSb. Crystals, 2017, 7, 313.	2.2	5
14	A three-dimensional insight into correlation between carrier lifetime and surface recombination velocity for nanowires. Nanotechnology, 2018, 29, 504003.	2.6	5
15	Energy-Sensitive GaSb/AlAsSb Separate Absorption and Multiplication Avalanche Photodiodes for X-Ray and Gamma-Ray Detection. Advanced Optical Materials, 2019, 7, 1900107.	7.3	5
16	Lateral carrier transfer for high density InGaAs/GaAs surface quantum dots. Journal of Luminescence, 2020, 218, 116870.	3.1	5
17	Significant suppression of surface leakage in GaSb/AlAsSb heterostructure with Al <sub>2</sub> O <sub>3</sub> passivation. Japanese Journal of Applied Physics, 2019, 58, 090907.	1.5	3
18	Feasibility of room-temperature mid-wavelength infrared photodetectors using InAsSb nanostructured photoabsorbers. , 2018, , .		2

#	ARTICLE	IF	CITATIONS
19	Mapping Charge Recombination and the Effect of Point-Defect Insertion in GaAs Nanowire Heterojunctions. <i>Physical Review Applied</i> , 2021, 16, .	3.8	1
20	Inducing Electrically-Active Defects in a Gallium Arsenide Nanowire with an Electron Beam. <i>Microscopy and Microanalysis</i> , 2019, 25, 1618-1619.	0.4	0
21	Numerical analysis of nanowire surface recombination using a three-dimensional transient model. , 2018, , .		0